DRAM PART NUMBERING
- Ichon Site Product

HY 51 X XX XXX X X - XX XX

HYUNDAI I-Site
Memory Product

PRODUCT GROUP

51	: DRAM

PROCESS & POWER SUPPLY

BLANK	: CMOS, 5.0V
V	: CMOS, 3.3V

DENSITY & REFRESH

2	: 2M bits
4	: 4M bits
16	: 16M bits, 4K Ref.
17	: 16M bits, 2K Ref.
18	: 16M bits, 1K Ref.
64	: 64M bits, 8K Ref.
65	: 64M bits, 4K Ref.

DATA WIDTH & FEATURES

100	: x1(FP)	
400	: x4(FP)	
404	: x4(EDO)	
800	: x8(FP)	
804	: x8(EDO)	
160	: x16(FP)	
164	: x16(EDO)	
260	: x16(FP)	@ 2/4Mb
264	: x16(EDO)	@ 2/4Mb

SPEED

45	: 45ns
50	: 50ns
60	: 60ns
70	: 70ns

PACKAGE

J	: 300mil SOJ
JC	: 400mil SOJ
T	: 300mil TSOPII
TC	: 400mil TSOPII

POWER CONSUMPTION

BLANK	: Normal Power
L	: Low Power
SL	: Self Refresh with Low Power

DIE GENERATION

BLANK	: 1st Generation
A	: 2nd Generation
B	: 3rd Generation
C	: 4th Generation